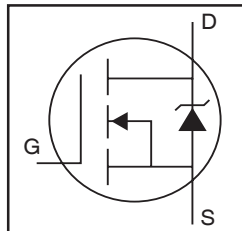


IRLR3636PbF IRLU3636PbF

Applications

- DC Motor Drive
- High Efficiency Synchronous Rectification in SMPS
- Uninterruptible Power Supply
- High Speed Power Switching
- Hard Switched and High Frequency Circuits

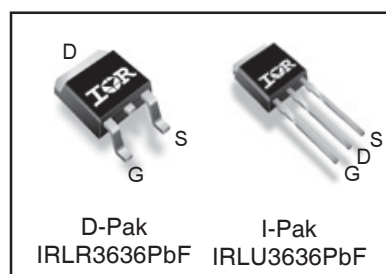
HEXFET® Power MOSFET



V_{DS}	60V
$R_{DS(on)}$ typ.	5.4mΩ
max.	6.8mΩ
I_D (Silicon Limited)	99A①
I_D (Package Limited)	50A

Benefits

- Optimized for Logic Level Drive
- Very Low $R_{DS(ON)}$ at 4.5V V_{GS}
- Superior R^*Q at 4.5V V_{GS}
- Improved Gate, Avalanche and Dynamic dV/dt Ruggedness
- Fully Characterized Capacitance and Avalanche SOA
- Enhanced body diode dV/dt and dI/dt Capability
- Lead-Free



G	D	S
Gate	Drain	Source

Absolute Maximum Ratings

Symbol	Parameter	Max.	Units
I_D @ $T_C = 25^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V (Silicon Limited)	99 ①	A
I_D @ $T_C = 100^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V (Silicon Limited)	70 ①	
I_D @ $T_C = 25^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V (Package Limited)	50	
I_{DM}	Pulsed Drain Current ②	396	
P_D @ $T_C = 25^\circ\text{C}$	Maximum Power Dissipation	143	W
	Linear Derating Factor	0.95	W/°C
V_{GS}	Gate-to-Source Voltage	±16	V
dv/dt	Peak Diode Recovery ④	22	V/ns
T_J	Operating Junction and	-55 to + 175	°C
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	

Avalanche Characteristics

E_{AS} (Thermally limited)	Single Pulse Avalanche Energy ③	170	mJ
I_{AR}	Avalanche Current ②	See Fig.14, 15, 22a, 22b	A
E_{AR}	Repetitive Avalanche Energy ②		mJ

Thermal Resistance

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case ⑨	—	1.05	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB Mount) ⑧	—	50	
$R_{\theta JA}$	Junction-to-Ambient	—	110	

Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	60	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.07	—	V/°C	Reference to 25°C , $I_D = 5mA$ ②
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	5.4	6.8	mΩ	$V_{GS} = 10V, I_D = 50A$ ⑤
		—	6.6	8.3		$V_{GS} = 4.5V, I_D = 50A$ ⑤
$V_{GS(th)}$	Gate Threshold Voltage	1.0	—	2.5	V	$V_{DS} = V_{GS}, I_D = 100\mu A$
I_{DSS}	Drain-to-Source Leakage Current	—	—	20	μA	$V_{DS} = 60V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 60V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 16V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -16V$
$R_{G(int)}$	Internal Gate Resistance	—	0.6	—	Ω	

Dynamic @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
g_{fs}	Forward Transconductance	31	—	—	S	$V_{DS} = 25V, I_D = 50A$
Q_g	Total Gate Charge	—	33	49	nC	$I_D = 50A$
Q_{gs}	Gate-to-Source Charge	—	11	—		$V_{DS} = 30V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	15	—		$V_{GS} = 4.5V$ ⑤
Q_{sync}	Total Gate Charge Sync. ($Q_g - Q_{gd}$)	—	18	—		$I_D = 50A, V_{DS} = 0V, V_{GS} = 4.5V$
$t_{d(on)}$	Turn-On Delay Time	—	45	—	ns	$V_{DD} = 39V$
t_r	Rise Time	—	216	—		$I_D = 50A$
$t_{d(off)}$	Turn-Off Delay Time	—	43	—		$R_G = 7.5 \Omega$
t_f	Fall Time	—	69	—		$V_{GS} = 4.5V$ ⑤
C_{iss}	Input Capacitance	—	3779	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	332	—		$V_{DS} = 50V$
C_{rss}	Reverse Transfer Capacitance	—	163	—		$f = 1.0MHz$
$C_{oss \text{ eff. (ER)}}$	Effective Output Capacitance (Energy Related) ⑦	—	437	—		$V_{GS} = 0V, V_{DS} = 0V \text{ to } 48V$ ⑦, See Fig.11
$C_{oss \text{ eff. (TR)}}$	Effective Output Capacitance (Time Related) ⑥	—	636	—		$V_{GS} = 0V, V_{DS} = 0V \text{ to } 48V$ ⑥

Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	99	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ②	—	—	396		
V_{SD}	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}, I_S = 50A, V_{GS} = 0V$ ⑤
t_{rr}	Reverse Recovery Time	—	27	—	ns	$T_J = 25^\circ\text{C}$ $V_R = 51V,$
		—	32	—		$T_J = 125^\circ\text{C}$ $I_F = 50A$
Q_{rr}	Reverse Recovery Charge	—	31	—	nC	$T_J = 25^\circ\text{C}$ $di/dt = 100A/\mu s$ ⑤
		—	43	—		$T_J = 125^\circ\text{C}$
I_{RRM}	Reverse Recovery Current	—	2.1	—	A	$T_J = 25^\circ\text{C}$
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

- ① Calculated continuous current based on maximum allowable junction temperature Bond wire current limit is 50A. Note that current limitation arising from heating of the device leads may occur with some lead mounting arrangements.
- ② Repetitive rating; pulse width limited by max. junction temperature.
- ③ Limited by T_{Jmax} , starting $T_J = 25^\circ\text{C}$, $L = 0.136 \text{ mH}$
 $R_G = 25\Omega$, $I_{AS} = 50A$, $V_{GS} = 10V$. Part not recommended for use above this value.
- ④ $I_{SD} \leq 50A$, $di/dt \leq 1109 \text{ A}/\mu s$, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq 175^\circ\text{C}$.

- ⑤ Pulse width $\leq 400\mu s$; duty cycle $\leq 2\%$.
- ⑥ $C_{oss \text{ eff. (TR)}}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .
- ⑦ $C_{oss \text{ eff. (ER)}}$ is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .
- ⑧ When mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note # AN-994 techniques refer to application note #AN-994.
- ⑨ R_θ is measured at T_J approximately 90°C .

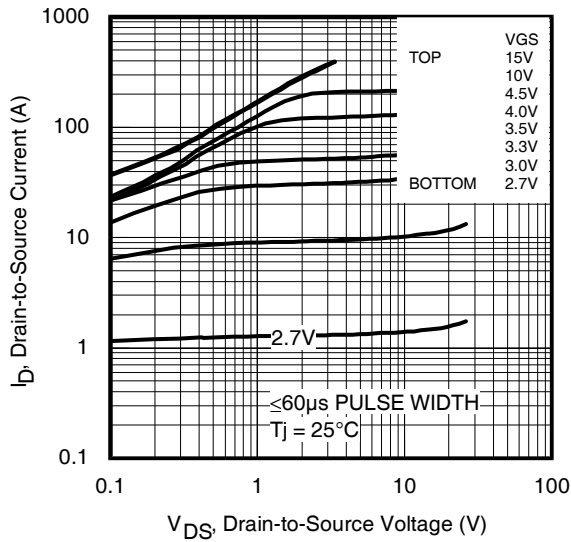


Fig 1. Typical Output Characteristics

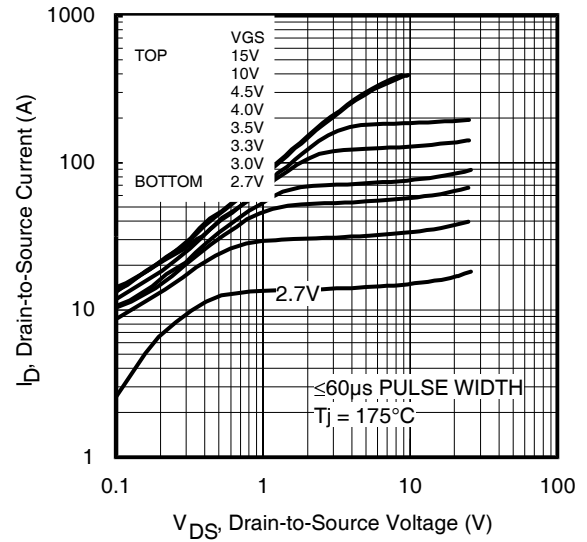


Fig 2. Typical Output Characteristics

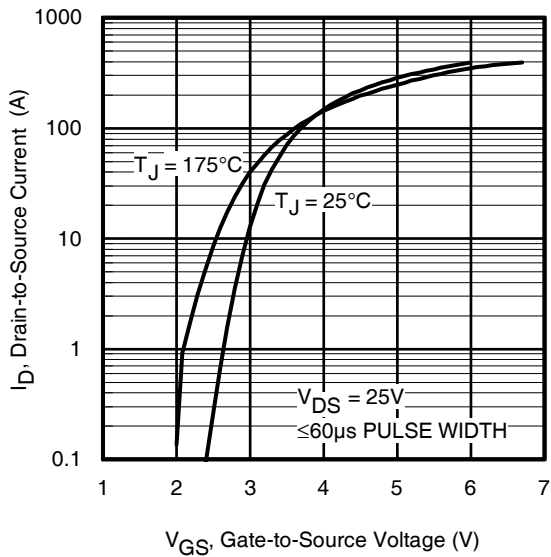


Fig 3. Typical Transfer Characteristics

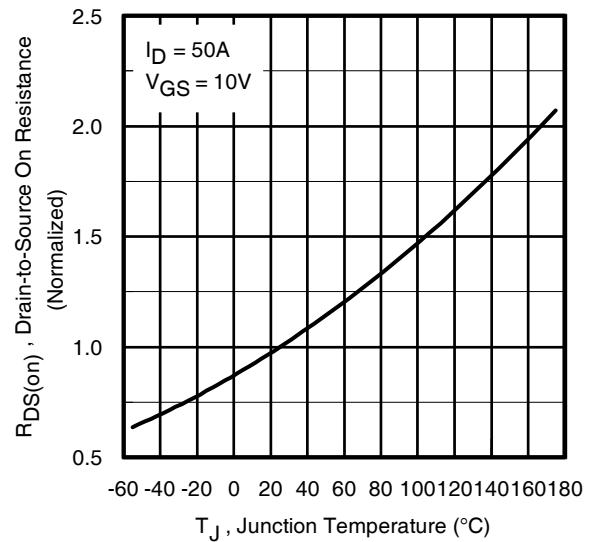


Fig 4. Normalized On-Resistance vs. Temperature

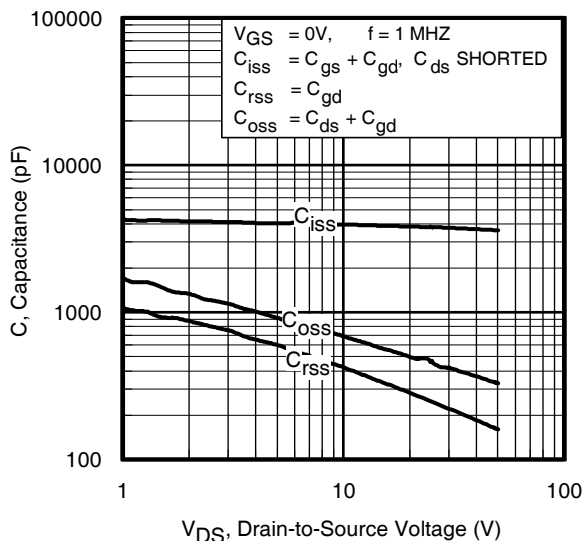


Fig 5. Typical Capacitance vs. Drain-to-Source Voltage

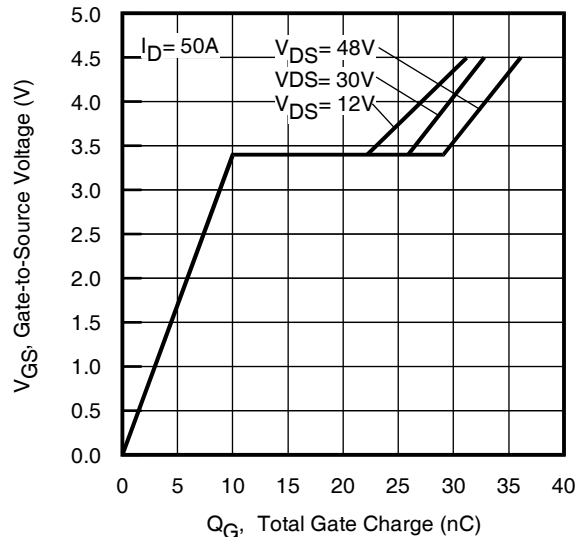


Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage

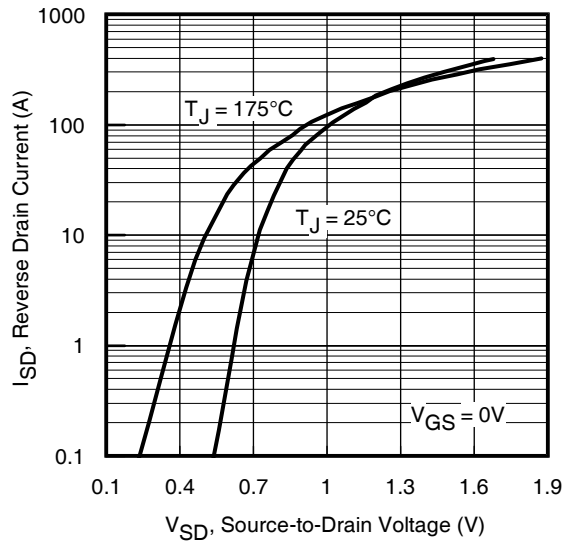


Fig 7. Typical Source-Drain Diode Forward Voltage

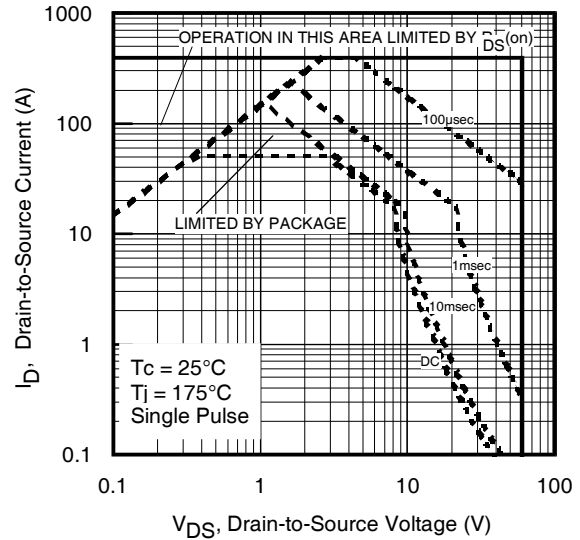


Fig 8. Maximum Safe Operating Area

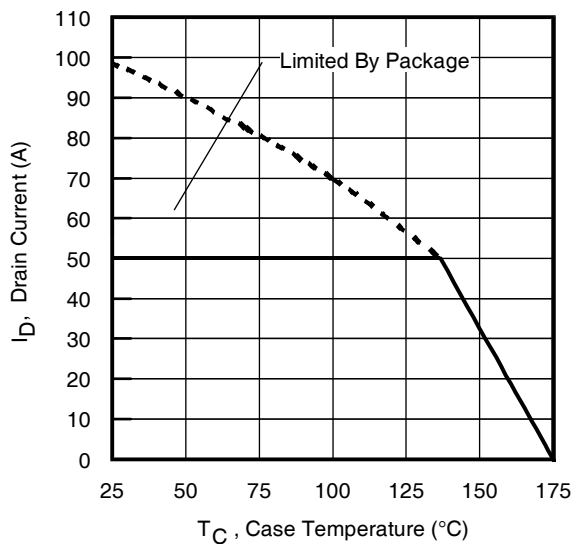


Fig 9. Maximum Drain Current vs. Case Temperature

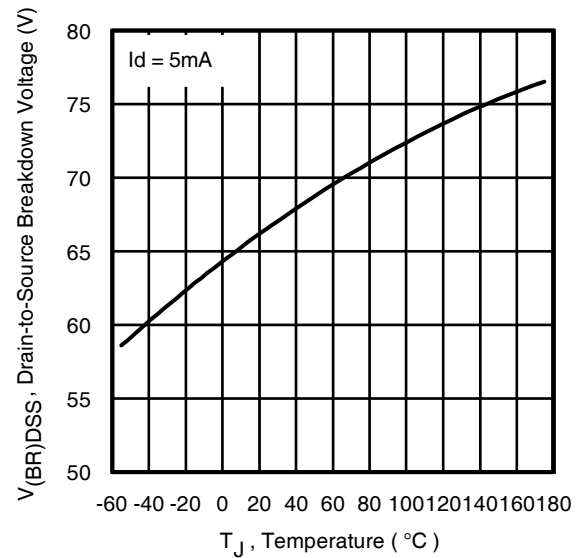


Fig 10. Drain-to-Source Breakdown Voltage

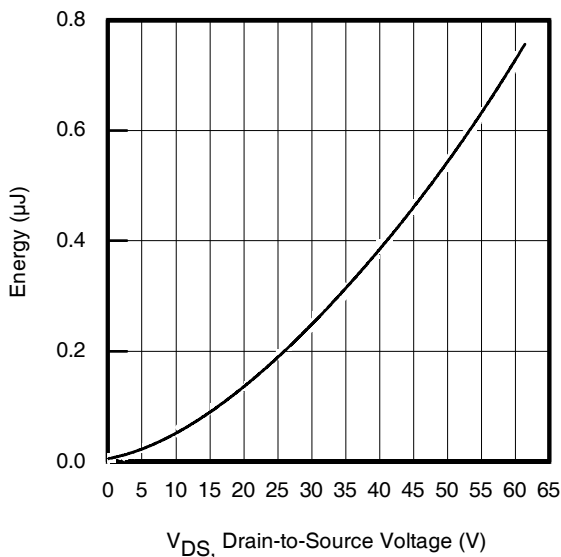


Fig 11. Typical C_{OSS} Stored Energy

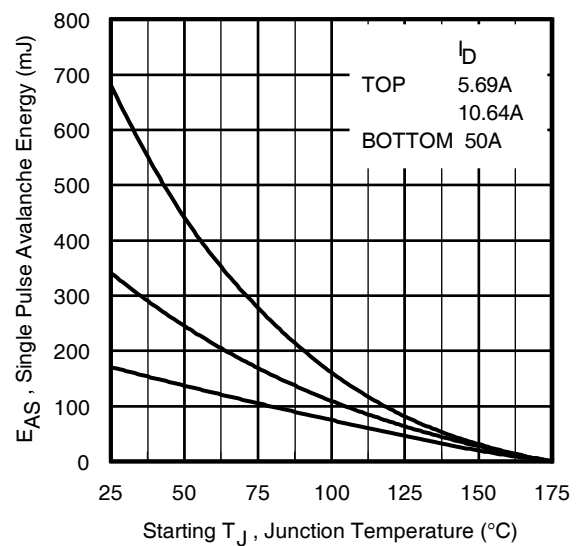


Fig 12. Maximum Avalanche Energy vs. Drain Current

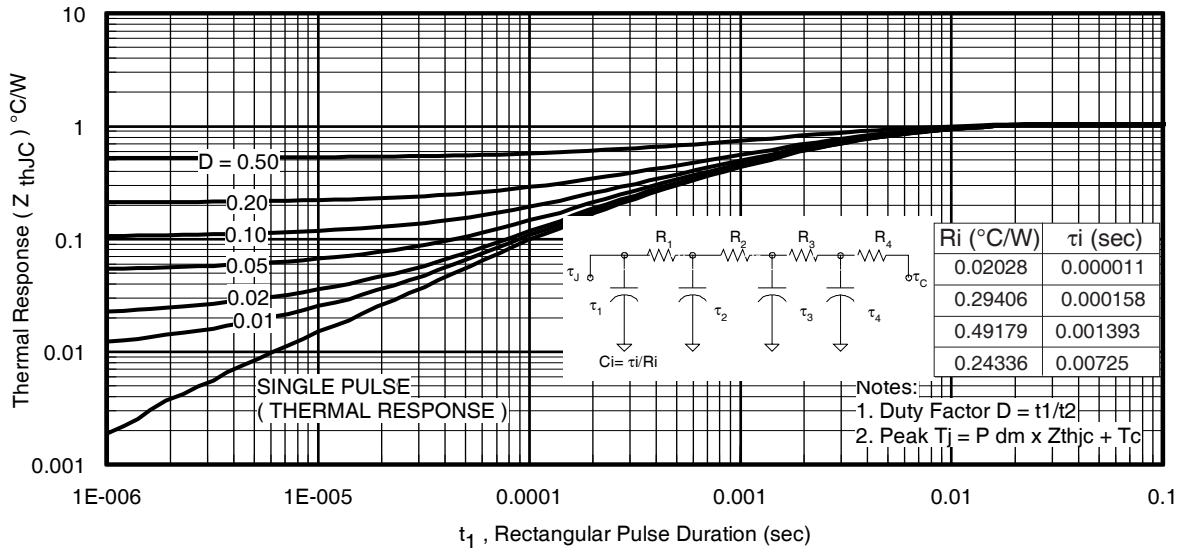


Fig 13. Maximum Effective Transient Thermal Impedance, Junction-to-Case

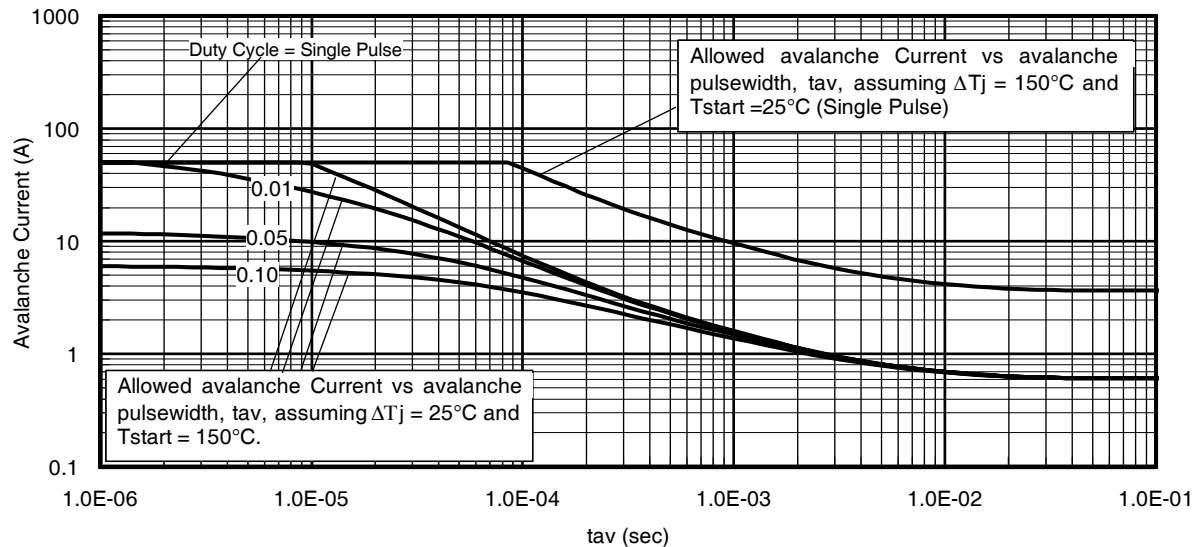


Fig 14. Typical Avalanche Current vs. Pulsewidth

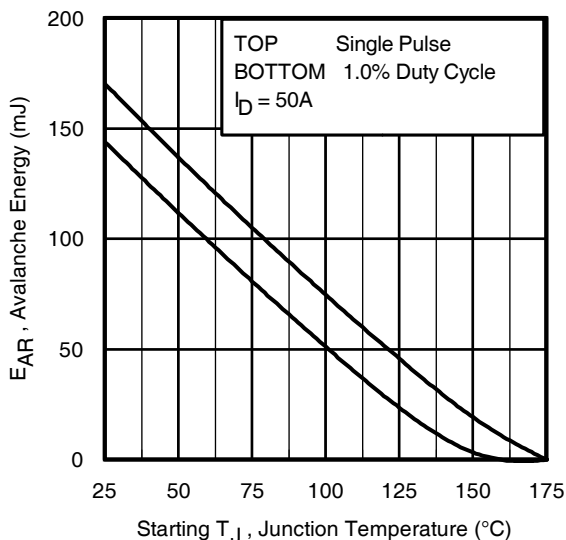


Fig 15. Maximum Avalanche Energy vs. Temperature

Notes on Repetitive Avalanche Curves , Figures 14, 15:
(For further info, see AN-1005 at www.irf.com)

1. Avalanche failures assumption:
Purely a thermal phenomenon and failure occurs at a temperature far in excess of T_{jmax} . This is validated for every part type.
2. Safe operation in Avalanche is allowed as long as T_{jmax} is not exceeded.
3. Equation below based on circuit and waveforms shown in Figures 16a, 16b.
4. $P_{D(ave)}$ = Average power dissipation per single avalanche pulse.
5. BV = Rated breakdown voltage (1.3 factor accounts for voltage increase during avalanche).
6. I_{av} = Allowable avalanche current.
7. ΔT = Allowable rise in junction temperature, not to exceed T_{jmax} (assumed as 25°C in Figure 14, 15).
 t_{av} = Average time in avalanche.
 D = Duty cycle in avalanche = $t_{av} \cdot f$
 $Z_{thJC}(D, t_{av})$ = Transient thermal resistance, see Figures 13)

$$P_{D(ave)} = 1/2 (1.3 \cdot BV \cdot I_{av}) = \Delta T / Z_{thJC}$$

$$I_{av} = 2\Delta T / [1.3 \cdot BV \cdot Z_{th}]$$

$$E_{AS(AR)} = P_{D(ave)} \cdot t_{av}$$

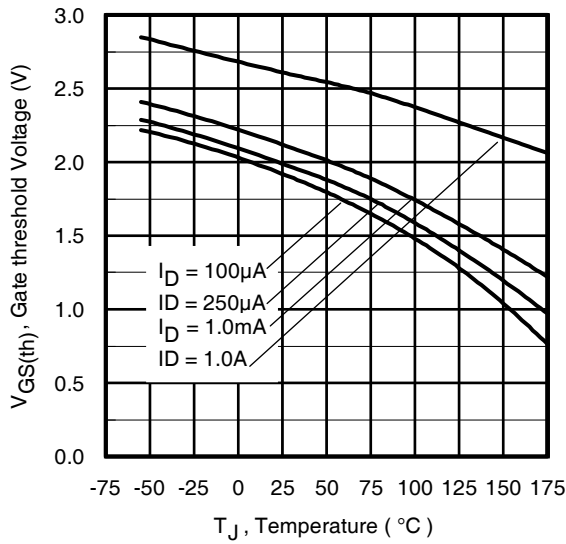


Fig. 16. Threshold Voltage vs. Temperature

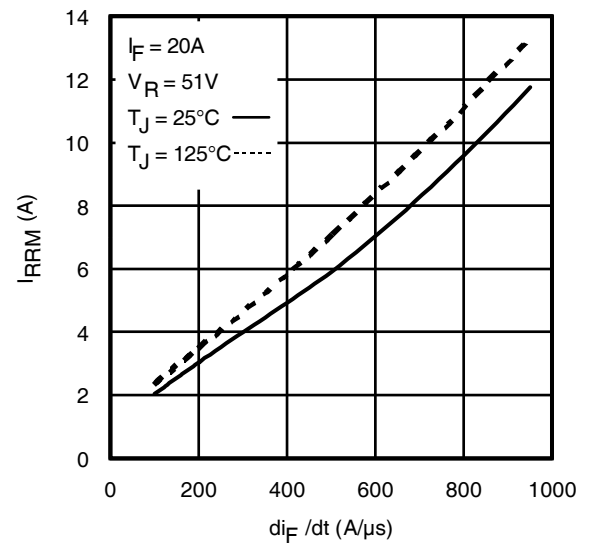


Fig. 17 - Typical Recovery Current vs. di_F/dt

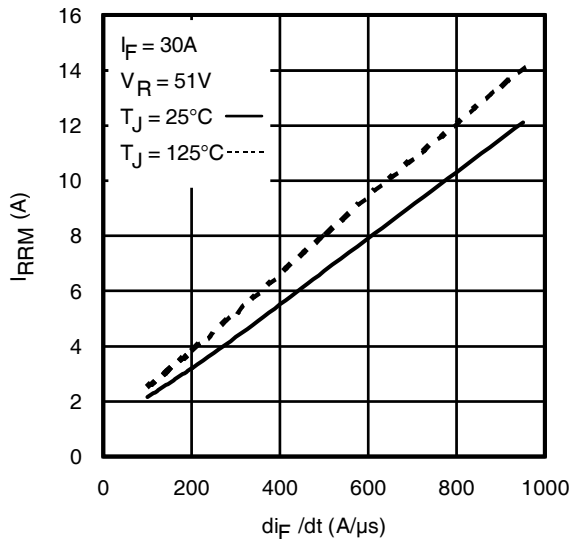


Fig. 18 - Typical Recovery Current vs. di_F/dt

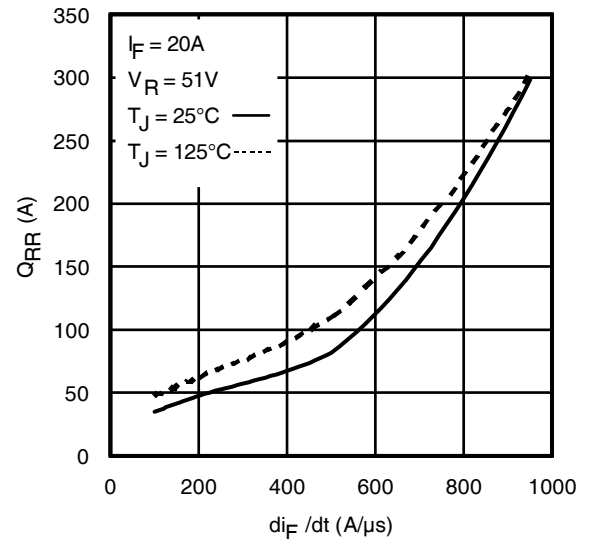


Fig. 19 - Typical Stored Charge vs. di_F/dt

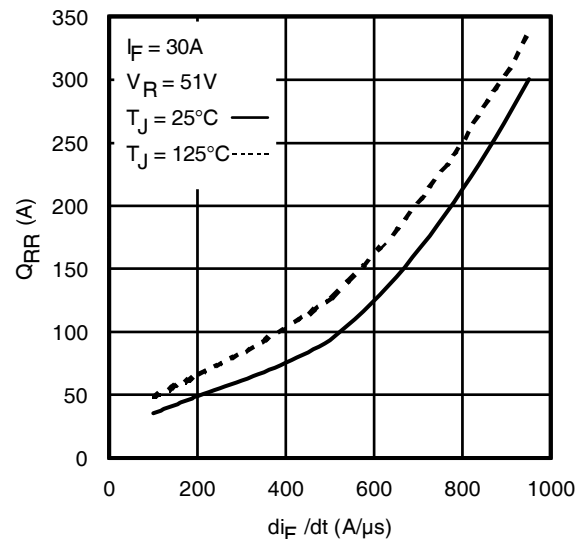


Fig. 20 - Typical Stored Charge vs. di_F/dt

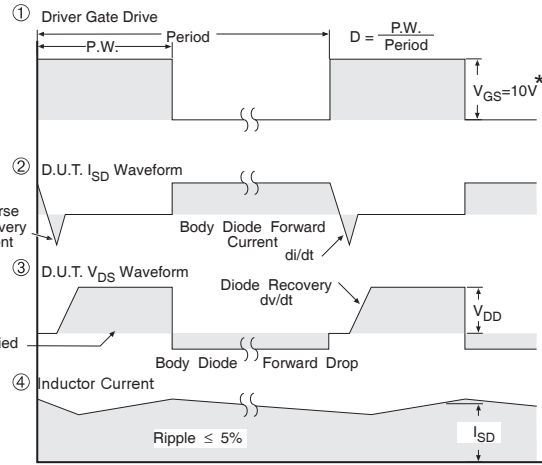


Fig 21. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs



Fig 22a. Unclamped Inductive Test Circuit



Fig 22b. Unclamped Inductive Waveforms



Fig 23a. Switching Time Test Circuit



Fig 23b. Switching Time Waveforms



Fig 24a. Gate Charge Test Circuit

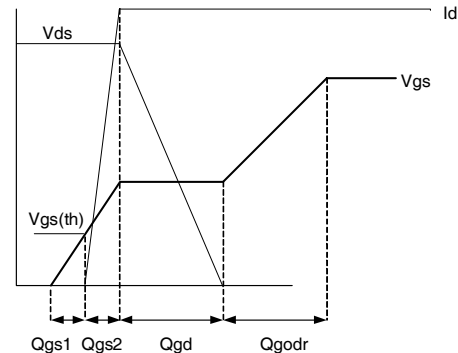
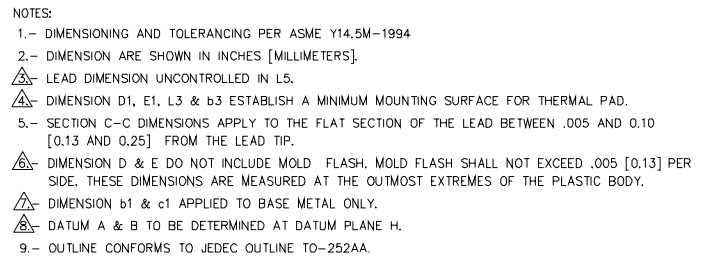


Fig 24b. Gate Charge Waveform

Dimensions are shown in millimeters (inches)

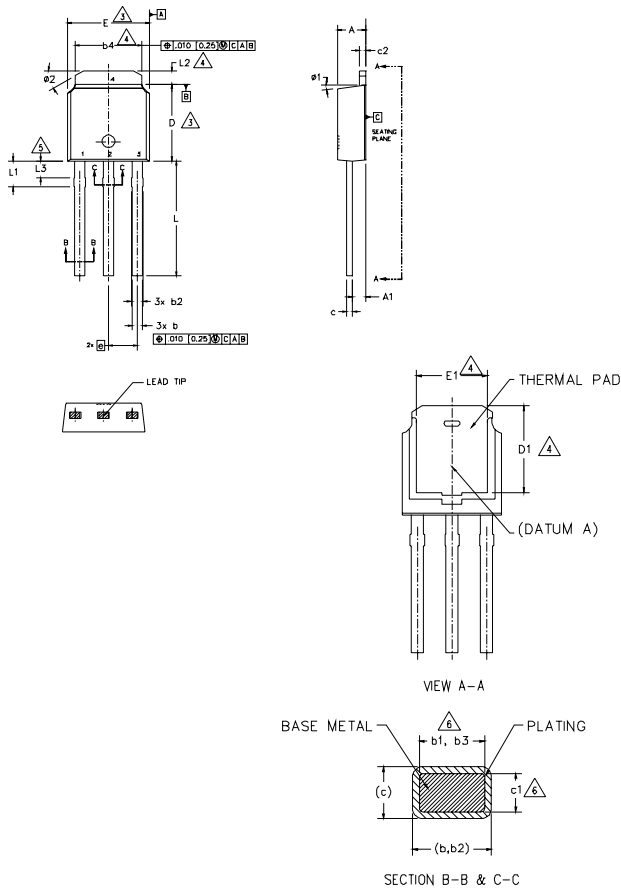


SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	2.18	2.39	.086	.094	
A1	—	0.13	—	.005	
b	0.64	0.89	.025	.035	
b1	0.65	0.79	.025	.031	7
b2	0.76	1.14	.030	.045	
b3	4.95	5.46	.195	.215	4
c	0.46	0.61	.018	.024	
c1	0.41	0.56	.016	.022	7
c2	0.46	0.89	.018	.035	
D	5.97	6.22	.235	.245	6
D1	5.21	—	.205	—	4
E	6.35	6.73	.250	.265	6
E1	4.32	—	.170	—	4
e	2.29 BSC		.090 BSC		
H	9.40	10.41	.370	.410	
L	1.40	1.78	.055	.070	
L1	2.74 BSC		.108 BSC		
L2	0.51 BSC		.020 BSC		
L3	0.89	1.27	.035	.050	4
L4	—	1.02	—	.040	
L5	1.14	1.52	.045	.060	3
ø	0"	10"	0"	10"	
ø1	0"	15"	0"	15"	
ø2	25"	35"	25"	35"	

www.irf.com

I-Pak (TO-251AA) Package Outline

Dimensions are shown in millimeters (inches)



NOTES:

- 1.- DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
- 2.- DIMENSIONS ARE SHOWN IN INCHES [MILLIMETERS]
- △ DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005 [0.13] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
- △ THERMAL PAD CONTOUR OPTION WITHIN DIMENSION b4, L2, E1 & D1.
- △ LEAD DIMENSION UNCONTROLLED IN L3.
- △ DIMENSION b1, b3 & c1 APPLY TO BASE METAL ONLY.
- 7.- OUTLINE CONFORMS TO JEDEC OUTLINE TO-251AA (Date 06/02).
- 8.- CONTROLLING DIMENSION : INCHES.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	2.18	2.39	.086	.094	6
A1	0.89	1.14	.035	.045	
b1	0.64	0.89	.025	.035	
b2	0.65	0.79	.025	.031	6
b3	0.76	1.14	.030	.045	
b4	0.76	1.04	.030	.041	
c	4.95	5.46	.195	.215	4
c1	0.46	0.61	.018	.024	
c2	0.41	0.56	.016	.022	
D	0.46	0.89	.018	.035	6
D1	5.97	6.22	.235	.245	
E	5.21	—	.205	—	
E1	6.35	6.73	.250	.265	3
e	4.32	—	.170	—	
L	2.29 BSC		.090 BSC		
L1	8.89	9.65	.350	.380	4
L2	1.91	2.29	.045	.090	
L3	0.89	1.27	.035	.050	
ø1	1.14	1.52	.045	.060	5
ø2	0"	15"	0"	15"	
	25"	35"	25"	35"	

LEAD ASSIGNMENTS

HEXFET

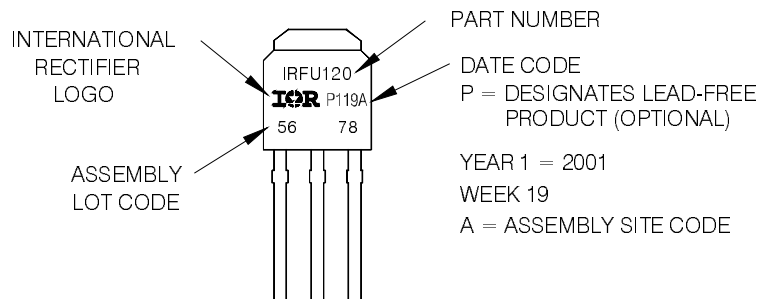
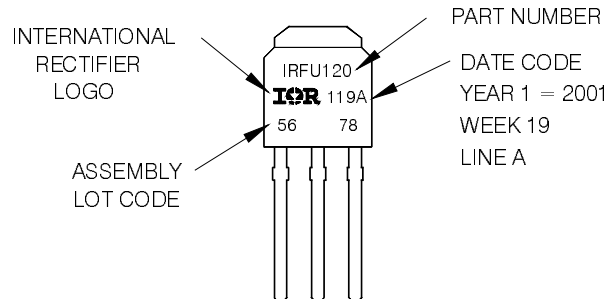
- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

I-Pak (TO-251AA) Part Marking Information

EXAMPLE: THIS IS AN IRFU120
WITH ASSEMBLY
LOT CODE 5678
ASSEMBLED ON WW 19, 2001
IN THE ASSEMBLY LINE "A"

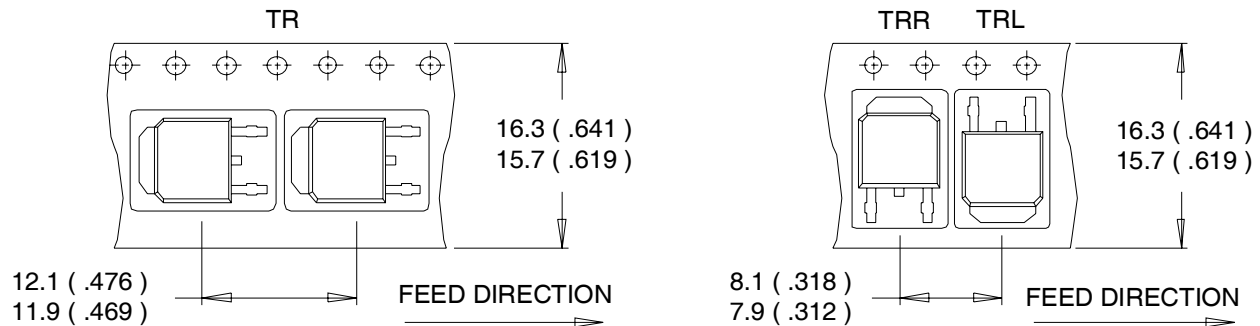
Note: "P" in assembly line position
indicates Lead-Free

OR



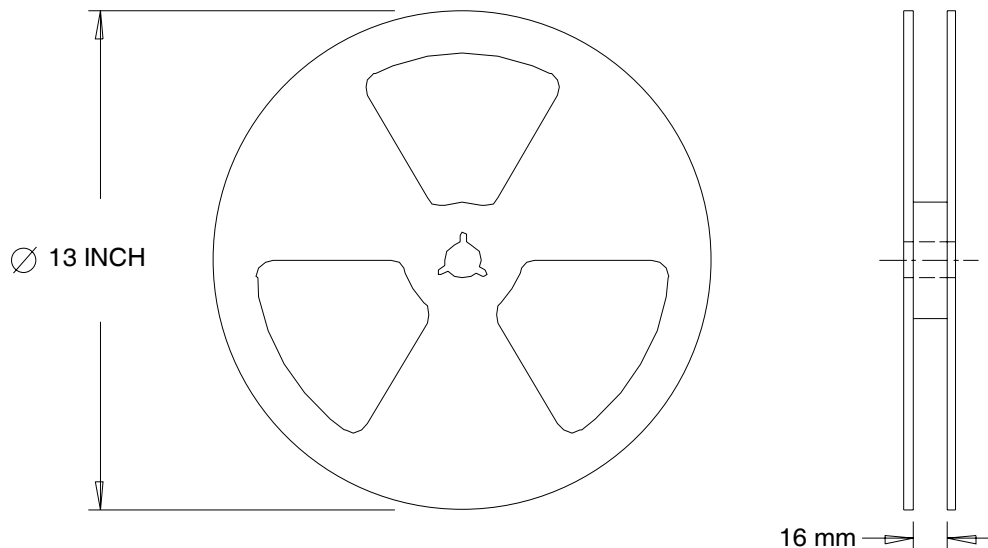
D-Pak (TO-252AA) Tape & Reel Information

Dimensions are shown in millimeters (inches)



NOTES :

1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



NOTES :

1. OUTLINE CONFORMS TO EIA-481.

Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

Data and specifications subject to change without notice.
This product has been designed and qualified for the Industrial market.
Qualification Standards can be found on IR's Web site.

International
IR Rectifier

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TAC Fax: (310) 252-7903

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